Single N-channel MOSFET

ELM4N6032FAA-N

■General description

ELM4N6032FAA-N uses advanced trench technology to provide excellent Rds(on), low gate charge and low gate threshold voltage.

■Features

- Vds=60V
- Id=13A (Vgs=10V)
- Rds(on) = 8.5mΩ (Vgs=10V)
- Rds(on) = 12.0mΩ (Vgs=4.5V)

■Maximum absolute ratings

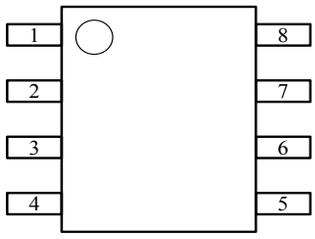
Parameter		Symbol	Limit	Unit	Note
Drain-source voltage		Vds	60	V	
Gate-source voltage		Vgs	±20	V	
Continuous drain current (Vgs=10V)	Ta=25°C	Id	13	A	1
	Ta=100°C		8		
Pulsed drain current		Idm	60	A	2
Single pulse avalanche energy		EAS	80	mJ	3
Avalanche current		Ias	40	A	
Power dissipation	Ta=25°C	Pd	2.7	W	4
Storage temperature range		Tstg	- 55 to 150	°C	
Operating junction temperature range		Tj	- 55 to 150	°C	

■Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Thermal resistance junction-to-ambient	t≤10s	Rθja	-	45	°C/W	1
	Steady state	Rθja	-	80		1

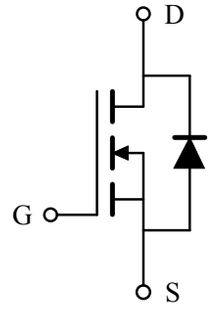
■Pin configuration

SOP-8(TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

■Circuit



■Electrical characteristics

Tj=25°C. Unless otherwise noted.

Parameter	Symbol	Condition		Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS								
Drain-source breakdown voltage	BVdss	Id=250μA, Vgs=0V		60	-	-	V	
Drain-source leakage current	Idss	Vds=48V, Vgs=0V		-	-	1	μA	
			Tj=55°C	-	-	5		
Gate-body leakage current	Igss	Vds=0V, Vgs=±20V		-	-	±100	nA	
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=250μA		1.2	-	2.5	V	
Static drain-source on-resistance	Rds(on)	Vgs=10V, Id=10A		-	-	8.5	mΩ	2
		Vgs=4.5V, Id=8A		-	-	12.0		
Forward transconductance	Gfs	Vds=5V, Id=10A		-	50	-	S	
Diode forward voltage	Vsd	Is=1A, Vgs=0V		-	-	1.2	V	2
Diode continuous source current	Is	Vgs=Vds=0V, Force current		-	-	10	A	1, 5
Pulsed source current	Ism			-	-	60	A	2, 5
DYNAMIC PARAMETERS								
Input capacitance	Ciss	Vgs=0V, Vds=25V, f=1MHz		-	3307	-	pF	
Output capacitance	Coss			-	201	-	pF	
Reverse transfer capacitance	Crss			-	151	-	pF	
SWITCHING PARAMETERS								
Total gate charge (10V)	Qg	Vgs=10V, Vds=48V, Id=10A		-	57.0	-	nC	
Gate-source charge	Qgs			-	8.7	-	nC	
Gate-drain charge	Qgd			-	14.0	-	nC	
Turn-on delay time	td(on)	Vgs=10V, Vds=30V, Id=10A, Rgen=3.3Ω		-	16.2	-	ns	
Turn-on rise time	tr			-	41.2	-	ns	
Turn-off delay time	td(off)			-	56.4	-	ns	
Turn-off fall time	tf			-	16.2	-	ns	
Reverse recovery time	trr	If=10A, di/dt=100A/μs		-	24.0	-	ns	
Reverse recovery charge	Qrr			-	15.0	-	nC	

Note :

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. The EAS data shows Max. rating . The test condition is Vdd=50V, Vgs=10V, L=0.1mH, Ias=40A.
4. The power dissipation is limited by 150°C junction temperature.
5. The data is theoretically the same as Id and Idm, in real applications, should be limited by total power dissipation.

■Typical electrical and thermal characteristics

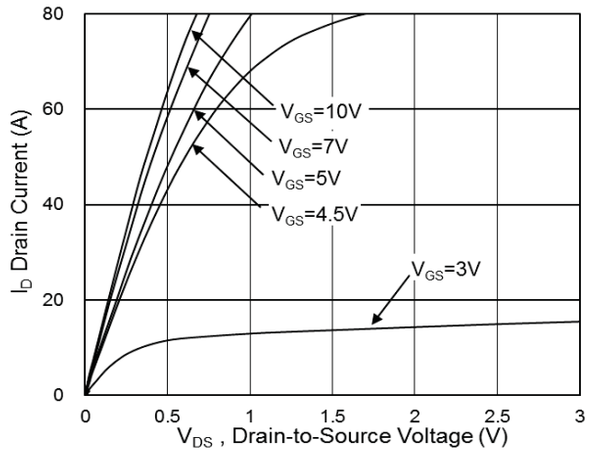


Fig.1 Typical Output Characteristics

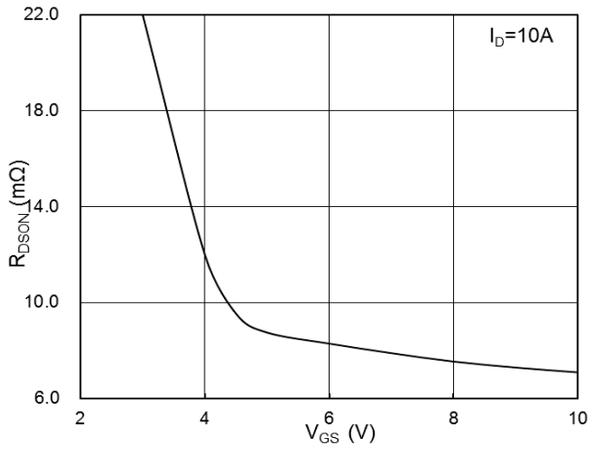


Fig.2 On-Resistance v.s Gate-Source Voltage

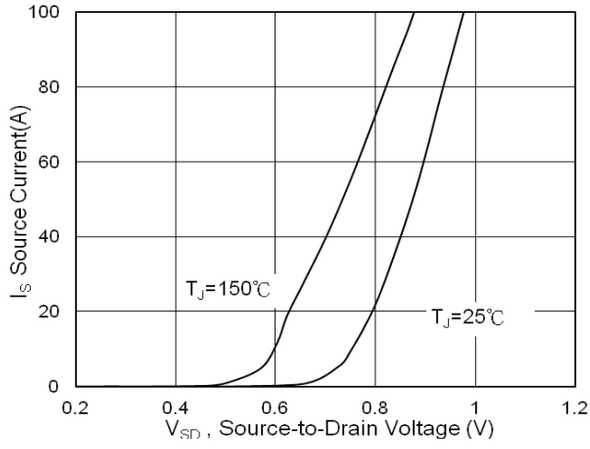


Fig.3 Forward Characteristics of Reverse

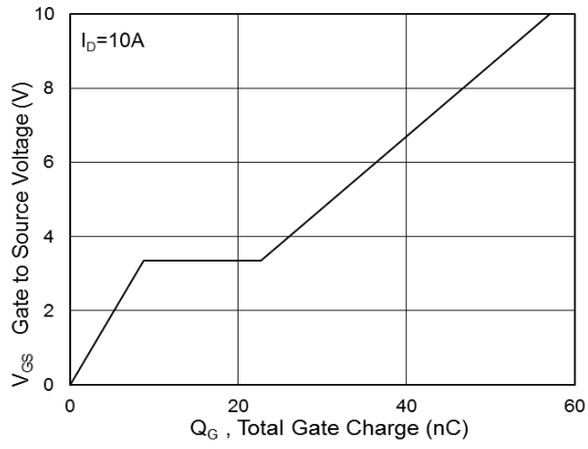


Fig.4 Gate-Charge Characteristics

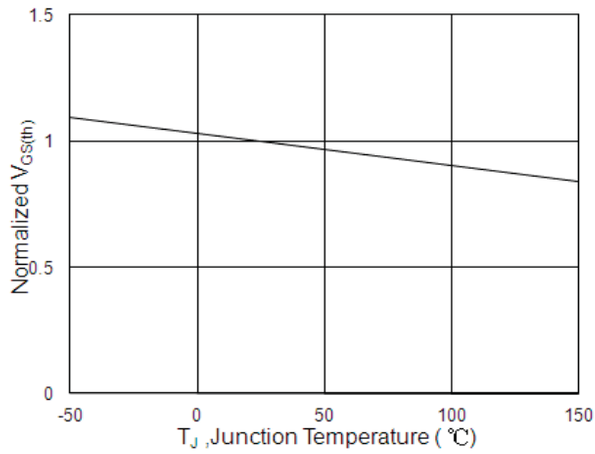


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

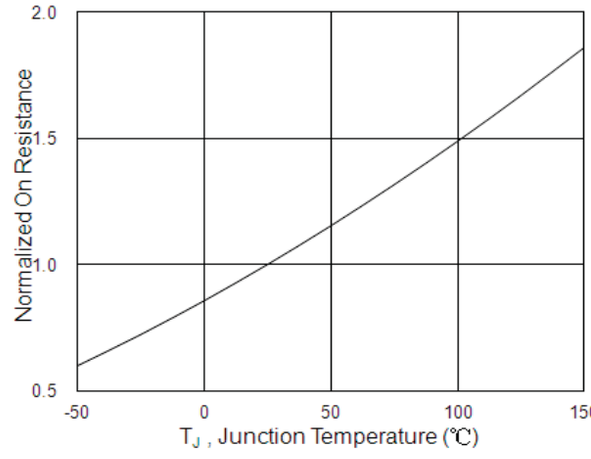


Fig.6 Normalized R_{DSON} vs. T_J

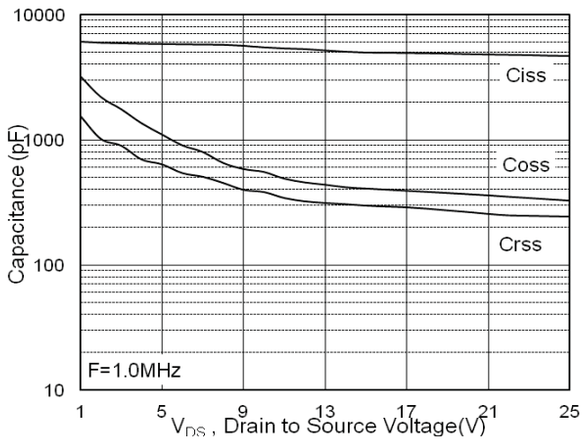


Fig.7 Capacitance

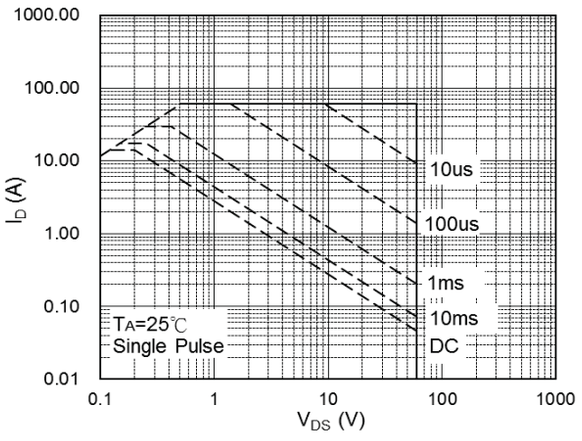


Fig.8 Safe Operating Area

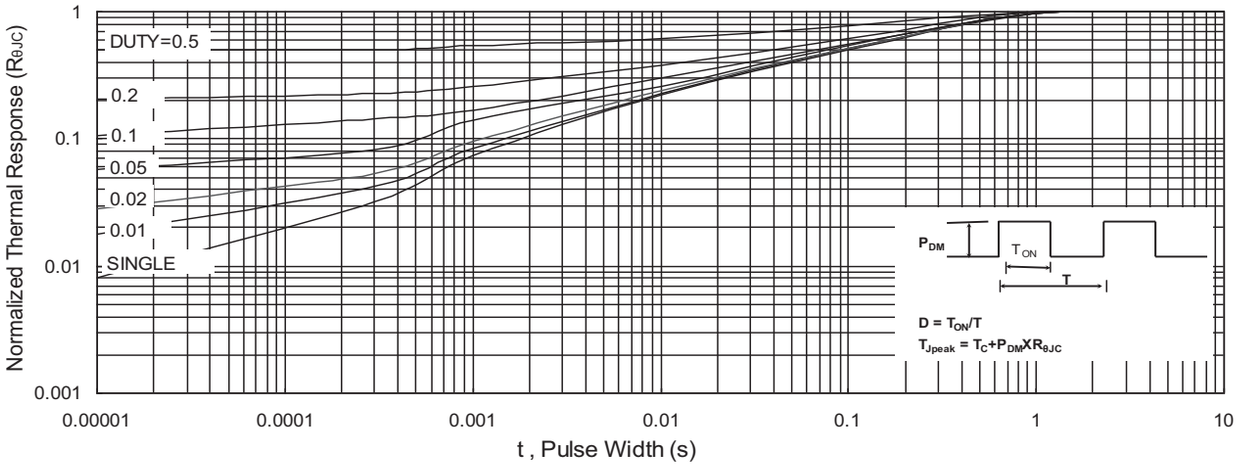


Fig.9 Normalized Maximum Transient Thermal Impedance

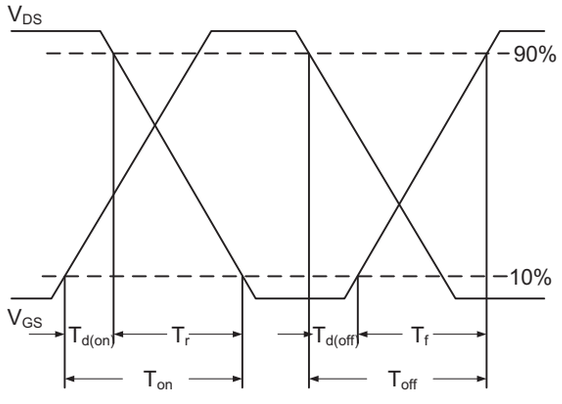


Fig.10 Switching Time Waveform

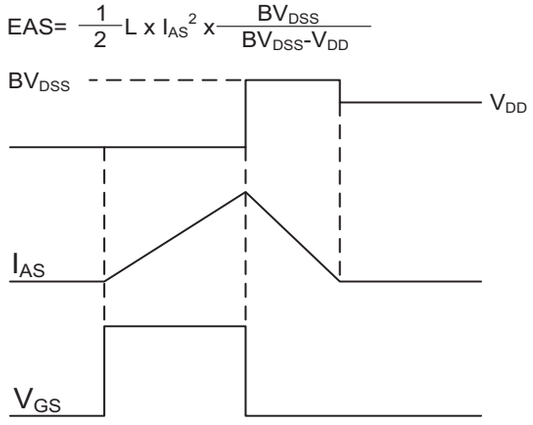


Fig.11 Unclamped Inductive Switching Waveform